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D ensity functional theory is widely used in surface science, but gives poor accuracy for surface energetics in m any cases. W e propose a practical strategy for using quantum M onte C arlo techniques to correct DFT predictions, and we demonstrate the operation of this strategy for the form ation energy of the M gO (001) surface and the adsorption energy of the H<sub>2</sub>O m olecule on this surface. W e note the possibility of applying the strategy to other surface problem s that m ay be a ected by large DFT errors.

For many years, electronic-structure techniques have played a major role in surface and interface science. The most widely used of these techniques is density functional theory (DFT) [1], which has been employed to study many problems, including metal-oxide adhesion, catalysis and corrosion. Yet there is evidence that com monly used DFT approximations are often seriously in error for basic quantities like surface form ation energies and molecular adsorption energies. It has been noted [2] that quantum Monte Carlo (QMC) techniques may be able to overcom e these problem s, because of their higher accuracy. We propose here a general strategy for using QMC to assess and correct DFT predictions for surface form ation and molecular adsorption energies, based on the idea that the important DFT errors are localised near the surface, so that the comparison of QMC with DFT for small systems may often su ce to give the inform ation needed. W e will show the practical operation of this strategy for the form ation energy of the M gO (001) surface and the adsorption energy of water on this surface, com paring where possible with experim ental data.

Insight into DFT errors for surface energetics com es from work on the jellium surface [3,4]. Jellium is the hom ogeneous interacting electron gas neutralised by a uniform background; its density n is characterised by the m ean inter-electron distance  $r_s$ , de ned by  $(4 r_s^3 = 3)n =$ 1, with r<sub>s</sub> in atom ic units. The planar jellium surface is form ed by having the neutralising background occupy only the half-space x < 0, so that the electron number density n (x) in the ground state goes to its bulk value n 1 and to 0 for x ! 1 . A courate results for forx! the form ation energy of the jellium surface have been obtained [4] by extrapolating QMC calculations on neutral jellium spheres of di erent radius R. The extrapolation was performed by studying the large-R behaviour of the di erence between the QMC total energy and the total energy calculated with DFT approximations, the main such approxim ations being: the local density approxim ation (LDA) [1]; the generalised gradient approximation (GGA) in the Perdew-Burke-Emzerhof form (PBE) [5];

and the m eta-GGA [6]. This jellium surface work showed that: (i) for 2  $r_s$  5, typical of sim ple m etals such as Aland Na, the m eta-GGA gives a very accurate surface energy , followed closely by LDA, with GGA being too low by a signi cant amount; (ii) as  $r_s$  falls below 2, the GGA errors rapidly worsen. In the region  $r_s$  1:5, characteristic of transition m etals and m any oxides, the GGA

is too low by  $0.3 \text{ Jm}^2$ , a serious error, because the surface energies of these m aterials are them selves in the region of 1 Jm<sup>2</sup>.

Indirect con m ation for large GGA errors in surface energies comes from a study [7] of the work of adhesion W<sub>adh</sub> of Pd (111) to  $-A l_2O_3$  (0001), for which accurate m easurem ents are available. (Here, W<sub>adh</sub> is the reversible work per unit area needed to separate the system containing the oxide-m etal interface into its m etal and oxide consituents.) The GGA value W<sub>adh</sub> = 1:6 J m<sup>2</sup> is far below the LDA and experimental values of 2.4 and 2.8 J m<sup>2</sup>. The authors argue [7] that the GGA error comes m ainly from errors in the free surface energies, and sem iquantitatively relate these errors to GGA errors for the jellium surface energies to correct DFT predictions for the surface energies of realm aterials [7].

The strategy we propose also uses QMC to correct DFT, but we apply QMC directly to the system of interest. In principle, QMC could be applied by brute force to the large slab system s commonly used to model surfaces in DFT calculations. However, since QMC is far more costly than DFT, this is not generally feasible at present. It is also unnecessary, and not the best way of gaining insight. Since DFT errors for surface energetics are expected to be localised in the surface region [8], an accurate assessment of these errors should be given by QMC calculations only on the atoms in the surface region. This implies that thin slabs, containing only a few atom ic layers, should su ce to assess the di erence between the surface energy given by QMC and by DFT approximations, so that this di erence will converge more rapidly with increasing slab thickness than the separate

surface energies. This strategy resembles that used to extract the energy of the jellium surface from calculations on jellium spheres [4]. We propose to use the same scheme for molecular adsorption energies. The molecule is placed on the surface of a thin slab, and we study the di erence between the QMC and DFT adsorption energies, seeking convergence of this di erence with increasing slab thickness.

W e have studied the practical feasibility of this strateqy for the formation energy of the M qO (001) surface. Our DFT calculations used the standard pseudopotential/plane-wave techniques [1], and were perform ed using the VASP code [9]. The surface was modelled using periodically repeated slab geom etry, the calculation conditions being characterised by basis-set com pleteness (plane-wave cut-o energy E<sub>cut</sub>), Brillouin-zone sam pling of the electronic states, the width L of the vacuum layer separating successive slabs, and the num ber of layers N layer in each slab. The surface form ation energy is =  $(E_{slab} \quad E_{bulk}) = A$ , with  $E_{slab}$  the energy of the slab system, per repeating cell,  $E_{bulk}$  the energy of the same number of atoms of the bulk material, and A the total surface area (both faces) of the slab, per repeating cell. This de nition applies for all N<sub>layer</sub> 1. The bulk energy E bulk is N layer times the bulk energy per layer e<sub>bulk</sub>, and it is convenient to obtain e<sub>bulk</sub> from the difference of E<sub>slab</sub> values for successive values of N<sub>laver</sub> in the lim it of large N<sub>laver</sub>. For given N<sub>laver</sub>, we always insist on convergence of the calculated with respect to  $\rm E_{cut}$  , BZ sampling and L to within 0.01 J m  $^2$  (this to – erance is satis ed for L > 6A). As expected from earlier work, for M gO (001) converges rapidly with respect to N  $_{\rm layer}$ , the residual errors being below 0.01 J m  $^2$  for N<sub>laver</sub> 2. For a given DFT approximation, the calculated depends a little on M gO lattice parameter a<sub>0</sub>. For the experimental value  $a_0 = 421 \text{ A}$ , we obtain = 124and  $0.87 \text{ Jm}^2$  with LDA and GGA (PBE) respectively. The di erence of 0.37 J m  $^2$  between the two is very sim – ilar to the di erence of  $0.4 \text{ Jm}^2$  between the LDA and GGA surface energies of  $-A l_2 O_3$  (0001) [7].

The calculation of by QMC is not standard, and we are not aware of previous calculations of for any oxide surface using QMC, though our recent QMC calculations on perfect and defective M gO crystals [10] indicated the feasibility of the present calculations. We refer the reader to reviews for details of QMC (e.g. [11]). W e recall that for high-precision results it is essential to use di usion M onte Carlo (DMC), in which the m anyelectron wavefunction is evolved in im aginary time, starting from an optim ised trial wavefunction generated in prior variational M onte C arlo calculations. The only error inherent in DMC is \ xed-node" error, due to the fact the nodes of the many-electron wavefunction are constrained to be those of the trial wavefunction. For many systems, including jellium, the evidence is that xed-node error is extremely small. For wide-gap system s such as M gO, the errors should be no greater. O ur calculations were perform ed with the casino code [12], using the same H artree-Fock pseudopotentials as in our previous work [10]. The trial wavefunctions were of the usual Slater-Jastrow type, with single-electron orbitals obtained with the plane-wave code PW SCF [13], generally using the large plane-wave cut-o of 4082 eV. These orbitals were represented in casino using the recently reported \blip-function" real-space basis set [14]. The DM C calculations all used a time-step of 0.005 a.u., and m ean number of walkers equal to 10,240. The calculations were done with free boundary conditions (i.e. no periodicity) norm alto the surface.

Our DMC calculations were perform ed on a series of M gO slabs with the num ber of layers N laver running from 1 to 5. For each N laver, convergence must be dem onstrated with respect to basis-set completeness and size of repeating surface unit cell. Basis-set errors with the blip basis set are readily m ade negligible, as show n earlier [14]. In DMC calculations, the wavefunctions are real, so that Brillouin-zone sam pling is generally impossible, and calculations are usually performed at the -point; this is why convergence with respect to size of surface unit cell must be checked. Our main DMC calculations used the 2 surface unit cell, for which the repeating cells con-2 tain from 16 (N  $_{layer} = 1$ ) to 80 (N  $_{layer} = 5$ ) ions; we show below that larger surface cells would give alm ost identical results.

The raw output from these calculations is DMC total energies  $E_{slab}^{DMC}$  for the ve  $N_{layer}$  values. Follow – ing our strategy, we now study the di erence  $E_{slab}$  $E_{slab}^{DMC} = E_{slab}^{DFT}$ , with the DFT slab energy calculated with exactly the same slab and the same ( -point) BZ sam pling as in the DMC calculations. Since the jellium results indicate that LDA surface energies are likely to be closer to DMC than those from GGA, we use LDA values for E  $_{\rm slab}^{\rm D\,F\,T}$  . W hen plotted against N  $_{\rm layer}$  , E  $_{\rm slab}$  will tend asymptotically (N  $_{\rm layer}$  ! 1 ) to a straight line, whose slope is equal to the di erence between the DMC and LDA bulk energies  $e_{bulk}$  per layer, and whose N layer = 0 intercept divided by A gives the di erence of DMC and DМС DFT.Since e<sub>bulk</sub> DFT surface energies is large, and since E slab contains the statistical errors of DMC, it is helpful to start this analysis by perform ing a least-squares straight-line ta + bN laver to the values of E  $_{\rm slab}$  , and then to use the resulting b value to form the quantity ~E <sub>slab</sub> E<sub>slab</sub> bN<sub>layer</sub>. The N<sub>layer</sub>! 1 straight-line asymptote of  $E_{slab}$  has the same N layer = 0 intercept as that of E slab. For N layer = 1;2;:::5, we nd the vevalues  $E_{slab} = 0.019(2), 0.009(6),$ 

0.007(9), 0.011(13) and 0.014(15) J m  $^2$ . This im – mediately shows that the DMC and LDA values of are almost exactly the same. W ithin our rather small statistical errors of at worst 0.015 J m  $^2$ , the di erence between the DMC and LDA surface energies has the very

small value of 0.01 J m  $^2$  . To check the errors due to use of the 2 2 surface cell (i.e. errors of BZ sam pling), we have performed LDA calculations on slabs having large surface cells with a series of N laver values, using -point sam pling. The values thus obtained di er from the LDA value extracted by similar -point calculations with the 2  $2 \text{ surface cell by only } 0.01 \text{ Jm}^2$ . The LDA value of for the lattice parameter we are using, converged with respect to BZ sampling and slab thickness, is 1.20 J m  $^2$  , and we conclude from our  $^{\sim}\mathrm{E}_{\mathrm{slab}}$  values that the fully converged DMC value is 1:19 0:01 Jm  $^2$  . M gO is one of the few oxides for which reasonably reliable experimental values of the surface energy are available [15]. Exploiting the fact that M gO cleaves readily along the (001) plane, the experiments measure the work of cleavage, thus ensuring that the results for cannot be in uenced by surface contam ination. Our DMC value of  $1.19 \, \text{Jm}^2$  is consistent with the measured values [15], which fall in the range 1.04 1.20 J m<sup>2</sup>.

In applying QMC to correct DFT predictions for the adsorption energy  $E_{ads}$  of  $H_2O$  on MgO (001), we assum e, in accord with experim ental and theoretical indications [16,17], that the molecule lies almost at on the surface, with the water O atom almost above a surface Mg ion, the water O {H bonds pointing towards surface 0 ions (Fig. 1). The adsorption energy is de ned to be  $E_{ads} = E_{H_2O} + E_{bare slab}$   $E_{slab+H_2O}$ , where the term s on the right are the energy of the isolated  $H_2O$  m olecule, the energy of the bare M gO (001) slab, and the energy of the slab with the H<sub>2</sub>O m olecule adsorbed on the surface, all three systems being fully relaxed to equilibrium. In our DFT calculations, we require that E ads be converged to within 10 meV with respect to plane-wave cut-o E<sub>cut</sub>, BZ sampling, and vacuum width L. Furtherm ore, since we want E<sub>ads</sub> for an isolated molecule, we exam ine the dependence of E ads on the size of the surface unit cell. We nd that with the 2 2 cell,  $E_{ads}$  is already converged to better than 10 m eV (this was tested by doing calculations up to 5 5 surface unit cells). With these tolerances always applied, we then study the dependence of E<sub>ads</sub> on the number of layers in the slab N layer. As N layer increases, E<sub>ads</sub> ceases to change by more than 2 meV for N layer 2.0 ur calculated values of E ads with LDA and GGA (PBE) are 0.92 and 0.43 eV respectively.

In the DMC calculations, we obtained  $E_{\rm H_2O}$  using periodically repeated cubes of di erent lengths d, with a single m olecule in each cube, using the m olecular geom etry taken from PBE (O {H bond length = 0.978 A, bond-angle = 104.4 ). There is a weak dipole-dipole correction, going as d<sup>3</sup>, but we extrapolate to in nite d to obtain  $E_{\rm H_2O}$  with a technical error uncertainty of only a few m eV. The slab energy  $E_{\rm bare \ slab}$  is taken from our DMC calculations on (see above). For H<sub>2</sub>O on the slab, strict application of our strategy would require us to use the relaxed con guration obtained from DMC calculations. We are not yet able to do this, since the calculation of

ionic forces with DMC is problem atic for the moment (though see Ref. [21]). Instead, we use a relaxed conguration from the DFT approximation which appears to reproduce DMC most closely. Our DFT calculations show that the relaxed height of the molecule above the surface di ens by 0:15A between LDA and PBE.We calculated the DMC energy fo  $H_2O$  on the 1-layer slab, with a series of geometries on a linear path between the relaxed LDA and PBE geometries, and we ind that the PBE geometry is very close to giving the lowest DMC energy. All our DMC results therefore refer to relaxed PBE geometries.

Since DFT calculations of E<sub>ads</sub> are converged with respect to surface cell size for 2 2 cells, our DMC calculations are all done with this surface cell. W ith N<sub>layer</sub> = 1, we nd  $E_{DMC}^{ads} = 0.63$  (3) eV,  $E_{PBE}^{ads} = 0.48$  eV, so that  $E^{ads} = E_{DMC}^{ads} = 0.15$  eV. For N<sub>layer</sub> = 2, the results are  $E_{DMC}^{ads} = 0.57$  (4) eV,  $E_{PBE}^{ads} = 0.42$  eV, so that  $E^{ads} = 0.15$  eV, identical to the N<sub>layer</sub> = 1 value within statistical errors. Using the N<sub>layer</sub> ! 1 PBE value of 0.43 eV, we thus estimate the N<sub>layer</sub> ! 1 DMC value as 0.58 (3) eV.

For E<sub>ads</sub>, a comparison with experiment can only be indicative at present. M easurem ents of LEED isotherm s and isobars for H<sub>2</sub>O adsorption on M gO (001) as a function of coverage, extrapolated to zero coverage gives  $E_{ads} = 0.52$  0:10 eV [18]. Tem perature program m ed desorption experiments show a peak at T = 235 260 K due to desorption of water at initial monolayer coverage [16,19]. The standard Redhead analysis, using the commonly assumed frequency prefactor of  $10^{13}\,\,\mathrm{sec}^{1}$  , yields an e ective E<sub>ads</sub> of 0:63 0:67 eV. However, this must include a signi cant contribution from attractive water-water interactions, so that  $E_{ads}$  for isolated  $H_2O$ should be som ew hat low er, and thus perhaps consistent with the LEED value of 0:52 0:10 eV. To com pare our DMC value with this, a correction for vibrational energies is needed. We have perform ed GGA (PBE) calculations on the adsorbed m olecule, which indicate that adsorption lowers the symmetric and asymmetric stretch modes of H<sub>2</sub>O by 12 and 9 THz respectively, and raises the bondbending mode by 2 THz. The associated zero-point energies raise the adsorption energy by 39 m eV. Translational and rotational energies of the  $H_2O$  m olecule in free space, and vibrations and librations of the adsorbed m olecule relative to the surface [20] raise and lower the adsorption energy by 64 m eV and 167 m eV respectively. A ltogether, vibrational e ects lower the adsorption energy by 64 m eV, so that our corrected DMC adsorption energy is 0.51 eV. Our calculated value thus appears to be consistent with the experim ental evidence, but clearly a more elaborate analysis would be needed to make this com parison robust. O ur com parisons m ake it fairly clear that LDA gives a serious overestim ate of the adsorption energy, while GGA (PBE) is considerably more accurate. Our proposed strategy is therefore feasible and useful for M gO surface energetics. M any other in portant problem s could be addressed in the sam e way, including the -A  $l_2O_3$  (0001) surface energy m entioned earlier [7]; the computationale ort needed for this case would similar to M gO. For this and other applications of the strategy, we believe that current progress in the calculation of ionic forces and structural relaxation with DM C [21] will be very helpful.

The ability to validate QMC against experiment for m olecular adsorption energies is limited by the lack of adequate techniques for putting m odelling and data into close contact. Progress in the ab initio prediction of TPD spectra [22] is encouraging in this respect. Finally, we note the importance of quantum chemistry methods. For wide-gap materials, techniques such as MP2 and CCSD (T) should deliver an accuracy similar to that ofDMC.Major improvements in the scaling of these techniques with number of atoms and size of basis sets [23] and to perform them in periodic boundary conditions [24] should make it possible to use them within our proposed strategy.

In summary, we have described a practical general strategy for using QMC calculations to assess and correct the errors of DFT approximations for the energetics of surfaces. Our calculations on the surface formation energy of MgO (001) and the adsorption energy of H $_2$ O on this surface con m the feasibility and usefulness of the strategy. The results support earlier inferences from the energetics of the jellium surface that the GGA surface formation energy for this type of material is substantially too low, and that LDA is more accurate. How ever, for the molecular adsorption energy, the reverse is true, with LDA errors being much greater than those of GGA.

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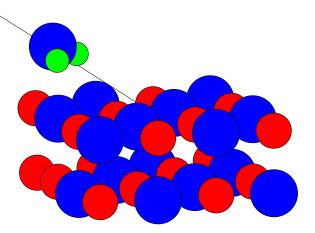


FIG.1. Adsorption geometry of the  $\rm H_2O$  molecule on M gO (001) from DFT with PBE exchange-correlation functional.